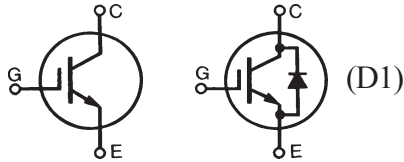


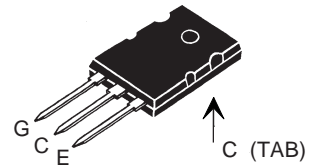
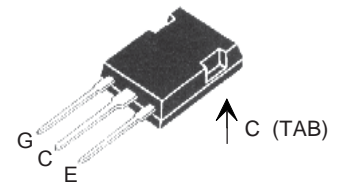
HiPerFAST™ IGBT

IXGK 35N120C
IXGX 35N120C
IXGK 35N120CD1
IXGX 35N120CD1

$$\begin{aligned}
 V_{CES} &= 1200 \text{ V} \\
 I_{C25} &= 70 \text{ A} \\
 V_{CE(sat)} &= 4.0 \text{ V} \\
 t_{fi(typ)} &= 115 \text{ ns}
 \end{aligned}$$



Symbol	Test Conditions	Maximum Ratings
V_{CES}	$T_J = 25^\circ\text{C to } 150^\circ\text{C}$	1200 V
V_{CGR}	$T_J = 25^\circ\text{C to } 150^\circ\text{C}; R_{GE} = 1 \text{ M}\Omega$	1200 V
V_{GES}	Continuous	± 20 V
V_{GEM}	Transient	± 30 V
I_{C25}	$T_C = 25^\circ\text{C}$	70 A
I_{C90}	$T_C = 90^\circ\text{C}$	35 A
I_{CM}	$T_C = 25^\circ\text{C}, 1 \text{ ms}$	140 A
SSOA (RBSOA)	$V_{GE} = 15 \text{ V}, T_{VJ} = 125^\circ\text{C}, R_G = 5 \Omega$ Clamped inductive load	$I_{CM} = 90$ @ $0.8 V_{CES}$ A
P_C	$T_C = 25^\circ\text{C}$	350 W
T_J		-55 ... +150 $^\circ\text{C}$
T_{JM}		150 $^\circ\text{C}$
T_{stg}		-55 ... +150 $^\circ\text{C}$
Maximum Lead temperature for soldering 1.6 mm (0.062 in.) from case for 10 s		300 $^\circ\text{C}$

TO-264 AA (IXGK)

PLUS 247™ (IXGX)


G = Gate, C = Collector,
 E = Emitter, TAB = Collector

M_d	Mounting torque (M3) (IXGK)	1.13/10Nm/lb.in.
Weight	TO-264 AA	10 g
	PLUS247™	6 g

Features

- International standard packages JEDEC TO-264 and PLUS247™
- Low switching losses, low $V_{(sat)}$
- MOS Gate turn-on - drive simplicity

Applications

- AC motor speed control
- DC servo and robot drives
- DC choppers
- Uninterruptible power supplies (UPS)
- Switched-mode and resonant-mode power supplies

Advantages

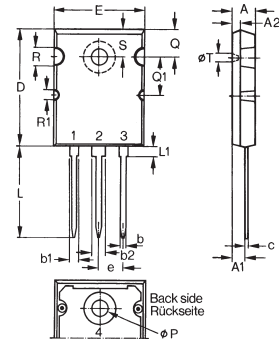
- High power density
- Easy to mount with 1 screw, (isolated mounting screw hole)
- Spring clip or clamp assembly possible.

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
BV_{CES}	$I_C = 1 \text{ mA}, V_{GE} = 0 \text{ V}$	1200		V
$V_{GE(th)}$	$I_C = 750 \mu\text{A}, V_{CE} = V_{GE}$	2.5		V
I_{CES}	$V_{CE} = V_{CES}, V_{GE} = 0 \text{ V}$	$T_J = 25^\circ\text{C}$		250 μA
		$T_J = 125^\circ\text{C}$		5 mA
I_{GES}	$V_{CE} = 0 \text{ V}, V_{GE} = \pm 20 \text{ V}$			± 100 nA
$V_{CE(sat)}$	$I_C = I_{C90}, V_{GE} = 15 \text{ V}$		3.2	4.0 V
				$T_J = 125^\circ\text{C}$

Symbol	Test Conditions	Characteristic Values			
		(T _J = 25°C, unless otherwise specified)			
		min.	typ.	max.	
g_{fs}	I _C = I _{C90} ; V _{CE} = 10 V, Pulse test, t ≤ 300 μs, duty cycle ≤ 2 %	30	40	S	
C_{ies}	V _{CE} = 25 V, V _{GE} = 0 V, f = 1 MHz		4620	pF	
C_{oes}			260	pF	
C_{res}			90	pF	
Q_g	I _C = I _{C90} , V _{GE} = 15 V, V _{CE} = 0.5 V _{CES}		170	nC	
Q_{ge}			28	nC	
Q_{gc}			57	nC	
t_{d(on)}	Inductive load, T_J = 25°C I _C = I _{C90} , V _{GE} = 15 V V _{CE} = 0.8 V _{CES} , R _G = R _{off} = 5 Ω Remarks: Switching times may increase for V _{CE} (Clamp) > 0.8 • V _{CES} , higher T _J or increased R _G		50	ns	
t_{ri}			27	ns	
t_{d(off)}			150	220	ns
t_{fi}			115	190	ns
E_{off}			3.0	4.2	mJ
t_{d(on)}	Inductive load, T_J = 125°C I _C = I _{C90} , V _{GE} = 15 V V _{CE} = 0.8 V _{CES} , R _G = R _{off} = 5 Ω Remarks: Switching times may increase for V _{CE} (Clamp) > 0.8 • V _{CES} , higher T _J or increased R _G		55	ns	
t_{ri}			31	ns	
E_{on}			2.6	mJ	
t_{d(off)}			220	ns	
t_{fi}			260	ns	
E_{off}		6.2	mJ		
R_{thJC}				0.35 K/W	
R_{thCK}			0.15	K/W	

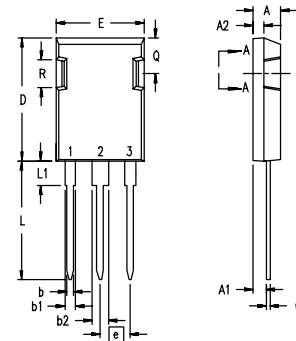
Symbol	Test Conditions	Characteristic Values		
		(T _J = 25°C, unless otherwise specified)		
		min.	typ.	max.
V_F	I _F = I _{C90} , V _{GE} = 0 V, Pulse test, t ≤ 300 μs, duty cycle d ≤ 2 %, T _J = 125°C			2.35 V
I_{RM}	I _F = I _{C90} , V _{GE} = 0 V, -di _F /dt = 480 A/μs V _R = 540 V I _F = 1 A; -di/dt = 200 A/μs; V _R = 30 V		32	36 A
t_{rr}		T _J = 100°C	225	ns
		T _J = 25°C	40	60
R_{thJC}				0.65 K/W

TO-264 AA Outline (IXGK)



Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.82	5.13	.190	.202
A1	2.54	2.89	.100	.114
A2	2.00	2.10	.079	.083
b	1.12	1.42	.044	.056
b1	2.39	2.69	.094	.106
b2	2.90	3.09	.114	.122
c	0.53	0.83	.021	.033
D	25.91	26.16	1.020	1.030
E	19.81	19.96	.780	.786
e	5.46 BSC		.215 BSC	
J	0.00	0.25	.000	.010
K	0.00	0.25	.000	.010
L	20.32	20.83	.800	.820
L1	2.29	2.59	.090	.102
P	3.17	3.66	.125	.144
Q	6.07	6.27	.239	.247
Q1	8.38	8.69	.330	.342
R	3.81	4.32	.150	.170
R1	1.78	2.29	.070	.090
S	6.04	6.30	.238	.248
T	1.57	1.83	.062	.072

PLUS247™ Outline (IXGX)



- Terminals: 1 - Gate
2 - Drain (Collector)
3 - Source (Emitter)
4 - Drain (Collector)

Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.83	5.21	.190	.205
A ₁	2.29	2.54	.090	.100
A ₂	1.91	2.16	.075	.085
b	1.14	1.40	.045	.055
b ₁	1.91	2.13	.075	.084
b ₂	2.92	3.12	.115	.123
C	0.61	0.80	.024	.031
D	20.80	21.34	.819	.840
E	15.75	16.13	.620	.635
e	5.45 BSC		.215 BSC	
L	19.81	20.32	.780	.800
L1	3.81	4.32	.150	.170
Q	5.59	6.20	.220	0.244
R	4.32	4.83	.170	.190

IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETS and IGBTs are covered by one or more of the following U.S. patents: 4,835,592 4,881,106 5,017,508 5,049,961 5,187,117 5,486,715 6,306,728B1
4,850,072 4,931,844 5,034,796 5,063,307 5,237,481 5,381,025